Attorney's Docket No.: 10559-586002 Cliem's Ref. No.: P12767C

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Lawrence D. Wong Art Unit : 2826

 Serial No. : 10/802,331
 Examiner : Scott Wilson

 Filed : March 16, 2004
 Conf. No. : 3745

Title : ELECTRON-BEAM TREATED CDO FILMS

MAIL STOP AMENDMENT Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Applicants request consideration of the references listed on the attached PTO-1449 form. Under 35 USC §120, this application relies on the earlier filing date of application serial number 10/161,104, filed on May 30, 2002. The following references were submitted to and/or cited by the Office in the prior application and, therefore, are not provided in this application.

This statement is being filed after a first Office action on the merits, but before receipt of a final Office action or a Notice of Allowance. Please apply the \$180 late submission fee of \$1.17(p) and any other charges or credits to Deposit Account No. 06-1050 referencing Attorney Docket Number 10559-586002.

Respectfully submitted,

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	Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office		Application No. 10/802,331
		sclosure Statement pplicant	Applicant Lawrence D. Wong	
(Use several sheets if necessary) (37 CFR §1.98(b))		Filing Date March 16, 2004	Group Art Unit 2826	

		***************************************	U.S. Pate	nt Documents			
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	4,848,141	07-1989	Oliver et al.	73	81	
	AB	6,340,628	01-2002	Van Cleemput et al.	438	586	
	AC						
	AD				Ī		

Foreign Patent Documents or Published Foreign Patent Applications								
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	AE							
	AF							
	AG							

	,	ocuments (include Author, Title, Date, and Place of Publication)
Examiner	Desig.	
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	AĦ	Here et al., "Mechanism of Mechanical and Chemical Polishing in Low Dielectric Constant Plasma Enhanced Chemical Vapor Deposition SiOC Layer from hexamethyldisiloxane", Electrochem. An Solid State Lett., 4(8):65-67 (Aug., 2001).
	AI	Music et al., "Synthesis and Mechanical Properties of Boron Suboxide Thin Films", J. Vac. Soi. Technol. A, 20(2):335-337 (Apr. 2002).
	AJ	Liu, P.T. et al., "The Effects of Plasma Treatment for Low Dielectric Constant Hydrogen Silsesquioxane (HSQ)", Thin Solid Films v. 332, pgs. 345-350 (1998).
	AK	Kondoh, E., "Structural Change in Porous Silica Thin Film after Plasma Treatment", Electrochem. and Solid-State Lett., 1(5):224-226 (1998).
	AL	Gidley et al., "Determination of pore-Size Distribution in Lew-Dielectric Thia Films", App. Phys. Lett., 76(10):1282-1284 (2000).
	AM	Loboda et al., "Using Trimethylsilane to Improve Safety, Throughput and Versatility in PECVD Processes", Electrochem. Proc., 97(10):443-453.
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	AP	Kanaya et al., "Penetration and Energy-Loss Theory of Electrons in Solid Targets", J. Phys. D.: Appl. Phys., vol. 5, pgs. 43-58 (1972).

Examinor Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if no	t in conformance and not considered. Include copy of this form with

next communication to applicant. Substitute Disclosure Form (PTO-1449)